



# PSMN057-200P

N-channel TrenchMOS SiliconMAX standard level FET

Rev. 02 — 4 January 2011

Product data sheet

## 1. Product profile

### 1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

### 1.3 Applications

- DC-to-DC converters
- Switched-mode power supplies

### 1.4 Quick reference data

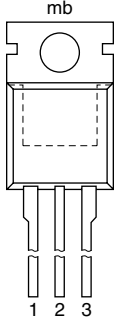
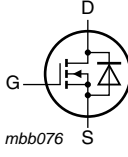
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	200	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$	-	-	39	A
$P_{tot}$	total power dissipation		-	-	250	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 17\text{ A}; T_j = 25\text{ °C}$	-	41	57	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 39\text{ A}; V_{DS} = 160\text{ V}; T_j = 25\text{ °C}$	-	37	50	nC



## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78 (TO-220AB)**

## 3. Ordering information

**Table 3. Ordering information**

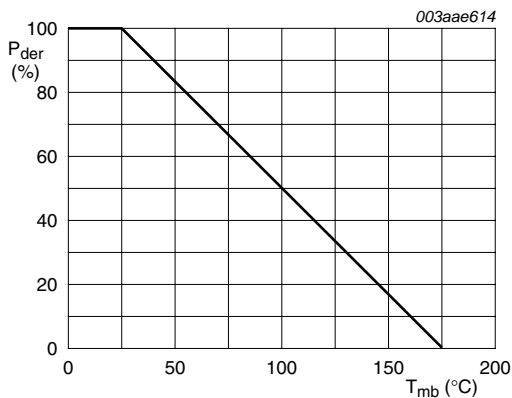
Type number	Package		
	Name	Description	Version
PSMN057-200P	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

**Table 4. Limiting values**

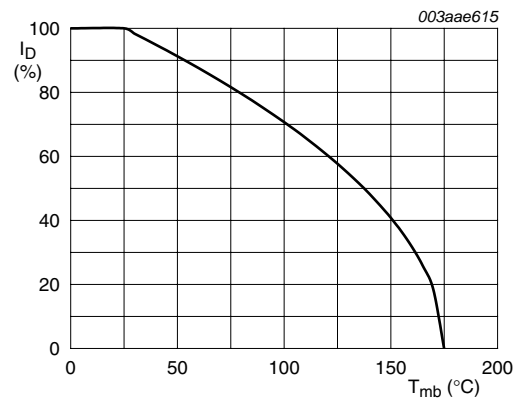
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	200	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	200	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$T_{mb} = 100\text{ °C}$	-	27.5	A
		$T_{mb} = 25\text{ °C}$	-	39	A
$I_{DM}$	peak drain current	pulsed; $T_{mb} = 25\text{ °C}$	-	156	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$	-	250	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	39	A
$I_{SM}$	peak source current	pulsed; $T_{mb} = 25\text{ °C}$	-	156	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 35\text{ A}; V_{sup} \leq 50\text{ V}; \text{unclamped}; t_p = 100\text{ }\mu\text{s}; R_{GS} = 50\text{ }\Omega$	-	300	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} \leq 50\text{ V}; V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; R_{GS} = 50\text{ }\Omega; \text{unclamped}$	-	35	A



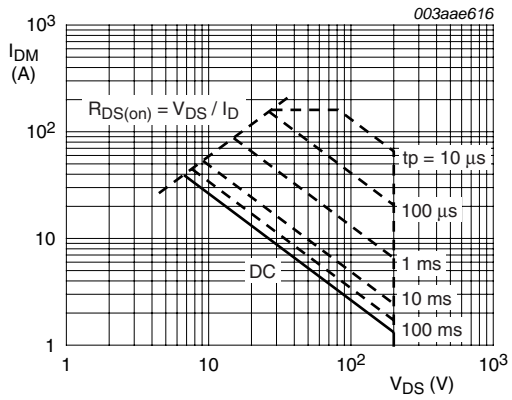
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of mounting base temperature**



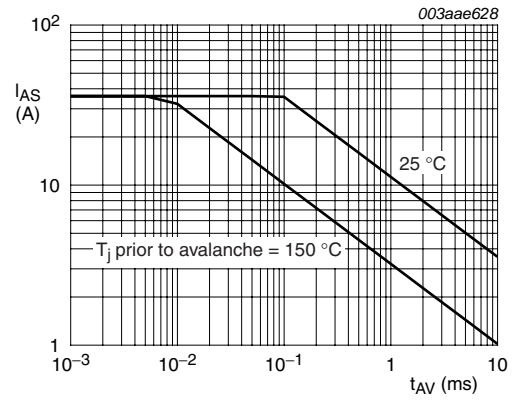
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

**Fig 2. Normalized continuous drain current as a function of mounting base temperature**



$T_{mb} = 25\text{ }^\circ\text{C}$ ;  $I_{DM}$  is single pulse

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**



unclamped inductive load

**Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period**

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

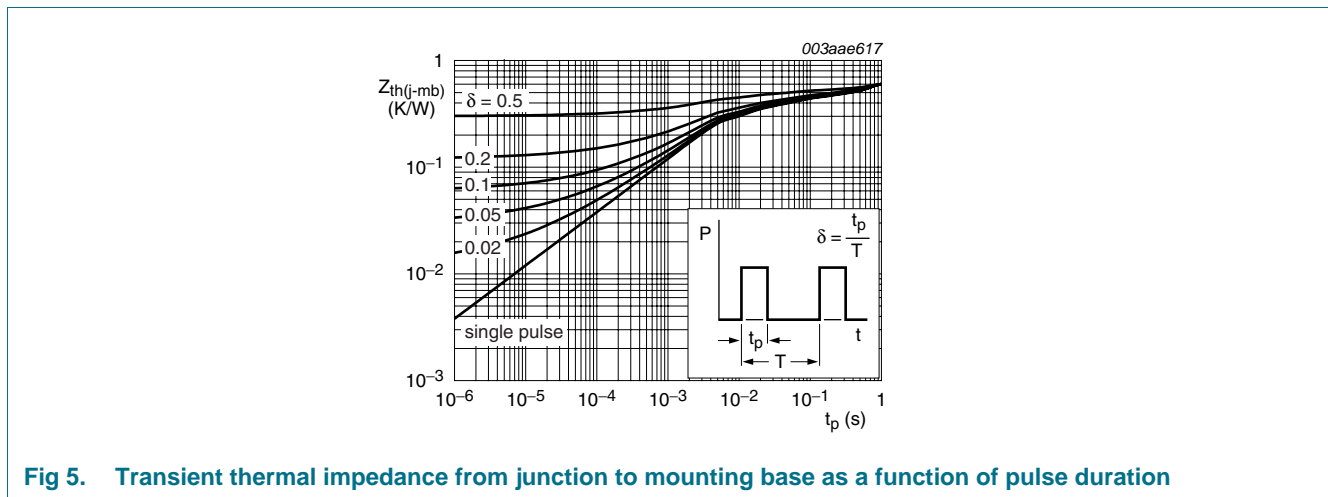


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	178	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	200	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C}$	-	-	6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C}$	2	3	4	V
$I_{DSS}$	drain leakage current	$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.03	10	$\mu\text{A}$
		$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 17 \text{ A}; T_j = 175 \text{ }^\circ\text{C}$	-	-	165	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 17 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	41	57	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 39 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	96	-	nC
$Q_{GS}$	gate-source charge		-	13	-	nC
$Q_{GD}$	gate-drain charge		-	37	50	nC
$C_{iss}$	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$	-	3750	-	pF
$C_{oss}$	output capacitance		-	385	-	pF
$C_{rss}$	reverse transfer capacitance		-	180	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 100 \text{ V}; R_L = 2.7 \text{ }^\circ\Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 5.6 \text{ }^\circ\Omega; T_j = 25 \text{ }^\circ\text{C}$	-	18	-	ns
$t_r$	rise time		-	58	-	ns
$t_{d(off)}$	turn-off delay time		-	105	-	ns
$t_f$	fall time		-	78	-	ns
$L_D$	internal drain inductance	measured from drain lead to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	4.5	-	nH
		measured from tab to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	3.5	-	nH
$L_S$	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ }^\circ\text{C}$	-	7.5	-	nH
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	133	-	ns
$Q_r$	recovered charge		-	895	-	nC

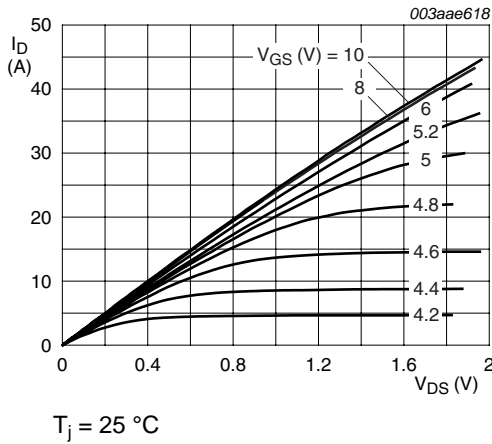


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

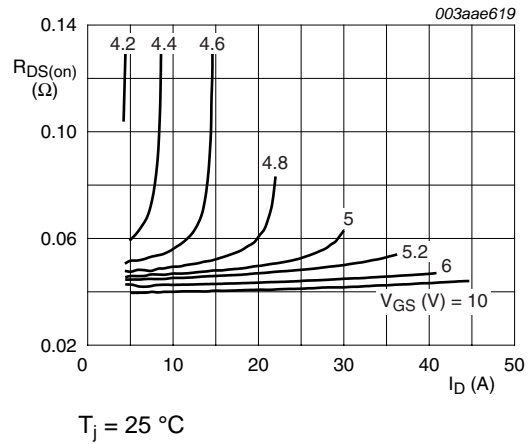


Fig 7. Drain-source on-state resistance as a function of drain current; typical values

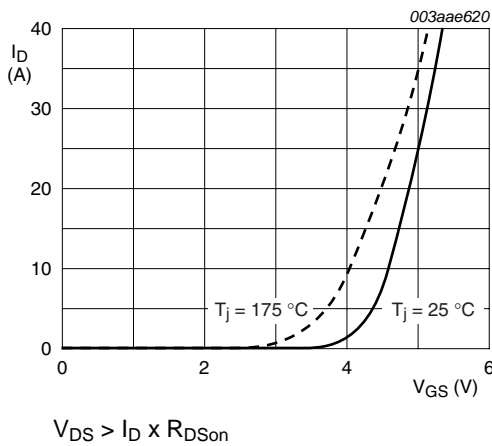


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

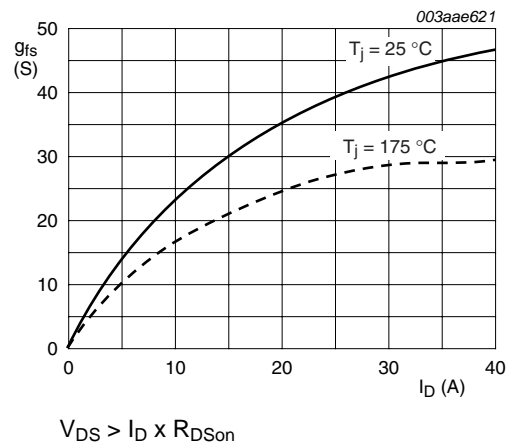
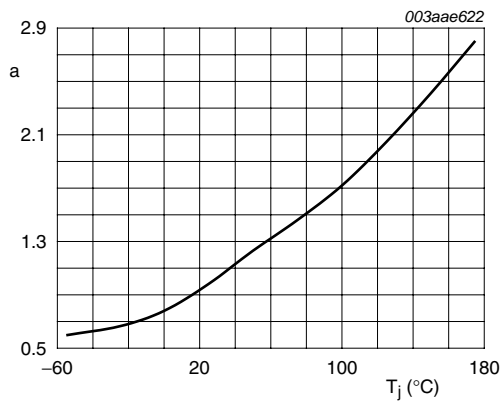


Fig 9. Forward transconductance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

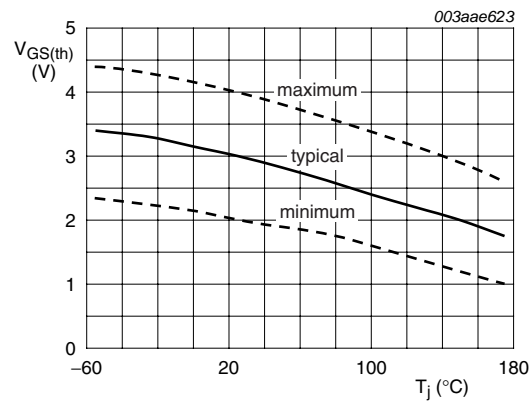
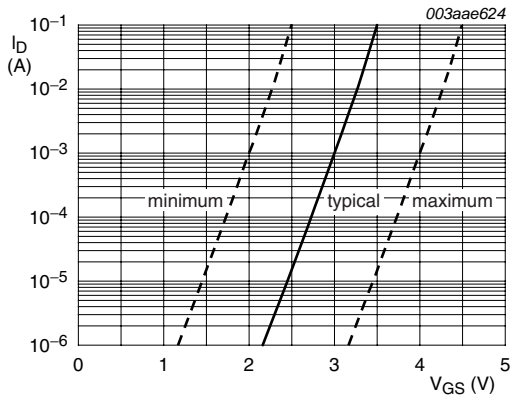
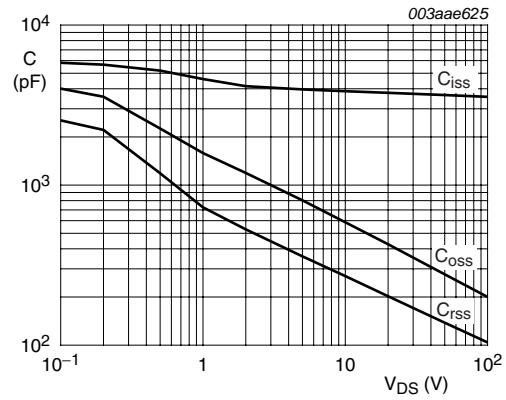


Fig 11. Gate-source threshold voltage as a function of junction temperature



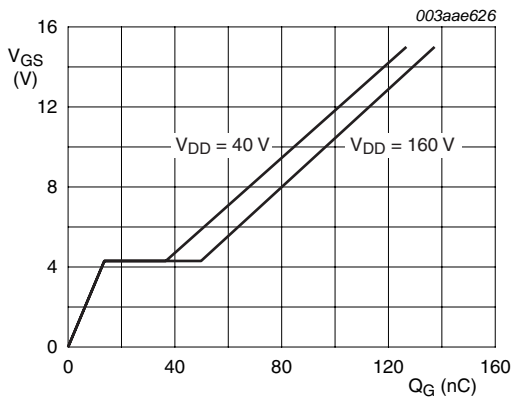
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = V_{GS}$

Fig 12. Sub-threshold drain current as a function of gate-source voltage



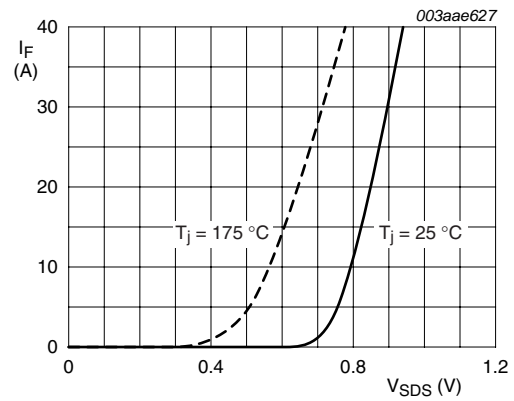
$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$T_j = 25\text{ }^\circ\text{C}; I_D = 39\text{ A}$

Fig 14. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}$

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values



7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

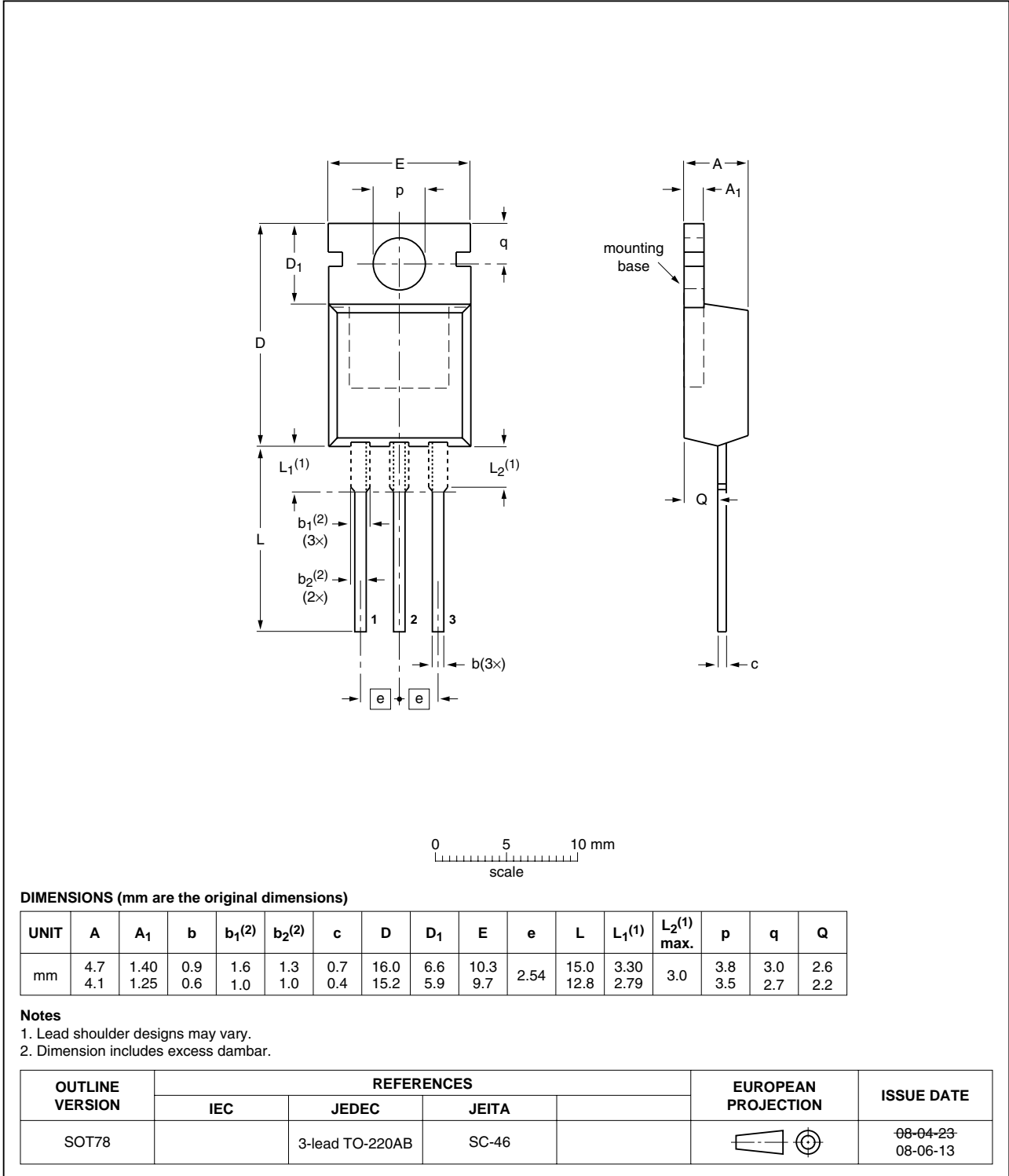


Fig 16. Package outline SOT78 (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN057-200P v.2	20110104	Product data sheet	-	PSMN057-200P v.1
Modifications:	<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li></ul>			
PSMN057-200P v.1	20000601	Product specification	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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